

**REMARKS**

Claims 1-18 are pending herein. The claims have been amended in order to more particularly point out, and distinctly claim the subject matter which the applicants regard as their invention.

Independent Claim 1, as amended, is to a substrate treating apparatus that has a processing chamber for processing at least one substrate, a substrate support member for supporting the at least one substrate, a prechamber for storing the substrate support member, and a control device for regulating a pressure to lower than atmospheric pressure during loading of the substrate support member supporting the at least one substrate from the prechamber into the processing chamber, wherein the substrate support member contains a support section, formed as a protrusion on the substrate support member and arranged to contact the substrate, and a receiving section installed below the support section and extending outwards from a section of the outer periphery of the support section. Independent Claim 5, as amended, is to a substrate treating apparatus that has a processing chamber for processing at least one substrate, a substrate support member for supporting the at least one substrate in the processing chamber, a heater for heating the at least one substrate in the processing chamber, and depositing a thin film on the at least one substrate by CVD method, wherein the substrate support member contains a support section, formed as a protrusion on the substrate support member, and arranged to contact the at least one substrate, and a receiving section formed below the support section and extending outwards from a section of the outer periphery of the support section, and the receiving section catches the particles generated on the support section. Independent Claim 9, as amended, is to a substrate treating apparatus that has a processing chamber

for processing at least one substrate, and a substrate support member for supporting the at least one substrate in the processing chamber, wherein the substrate support member contains a support section, formed as a protrusion on the substrate support member, and arranged to contact the substrate, and a receiving section formed below the support section and extending outwards from a section of the outer periphery of the support section, and the receiving section extends between 6 mm and 15 mm from a section of the outer periphery of the support section. Independent Claim 10, as amended, is to a substrate treating apparatus that has a processing chamber for processing at least one substrate, and a substrate support member for supporting the at least one substrate in the processing chamber, wherein the substrate support member contains a main section, and a support section, formed as a protrusion on the substrate support member, and arranged to contact the substrate, and a receiving section formed below the support section and extending outwards from a section of the outer periphery of the support section, and the main section, the support section, and the receiving section are integrated into one piece. Independent Claim 11, as amended, is to a manufacturing method for a semiconductor device. The method includes the steps of supporting at least one substrate in a substrate support member containing a support section, formed as a protrusion on the substrate support member, and arranged to contact the substrate, and a receiving section formed below the support section and extending outwards from a section of the outer periphery of the support section, loading the substrate support member supporting the at least one substrate at a pressure lower than atmospheric pressure from a prechamber into a processing chamber, processing the substrate supported by the substrate support member in the processing

chamber, and unloading the substrate support member supporting the substrate from the processing chamber. Independent Claim 15, as amended, is to a manufacturing method for a semiconductor device. The method includes the steps of loading at least one substrate into a processing chamber, supporting the at least one substrate by a substrate support member made up of a support section, formed as a protrusion on the substrate support member, and arranged to contact the substrate, and a receiving section formed below the support section and extending outwards from a section of the outer periphery of the support section for catching particles generated in the support section, depositing a thin film by CVD method on the at least one substrate supported by the substrate support member in the processing chamber, and unloading the substrate from the processing chamber.

In the Office Action, Claims 1-18 were rejected as anticipated under 35 U.S.C. 102(b) by ULVAC Japan Ltd. (JP 7-109574). Reconsideration and removal of this rejection are respectfully requested in view of the present claim amendments and the following remarks.

The Office Action alleges that the reference shows a substrate treating apparatus that has a processing chamber for processing at least one substrate, a substrate support member for supporting said at least one substrate, a prechamber for storing said substrate support member, and a control device for regulating the pressure to lower than atmospheric pressure during loading of said substrate support member supporting said at least one substrate from said prechamber into said processing chamber. It is also alleged the reference shows a substrate support member containing a support section to contact said substrate and a receiving section installed below said support section and

extending outwards from a section of the outer periphery of said support section, referring specifically to FIG. 1 and paragraphs 16 and 17 of the reference. It is also alleged the reference teaches the features of any of the independent Claims 1, 5, 9, 10, 11 and 15, as well as the dependent Claims 2-4, 6-8, 12-14 and 16-18.

Applicants respectfully submit that the reference fails to teach or suggest the present claimed apparatus or method. There is no protrusion that is formed on a substrate support member arranged to contact the substrate and a receiving section of the substrate support as in the present claims.

The section of the reference referred to in the Office Action (paragraphs 16 and 17) merely read, in the computer translation, as follows:

[0016] Drawing 1 shows one example of the device for enforcing this invention method, and one shows a load-locks type vertical type furnace among a figure.

[0017] And the load-locks type vertically type furnace 1 comprised the reserve exhaust room 2 which comprises the chamber made from stainless steel, and the furnace 3 which comprises the tube made from quartz, divided with the slice valve 4 between the reserve exhaust room 2 and the furnace 3, and made disengageable atmosphere in the reserve exhaust room 2 and the furnace 3.

This does not lead one to the specific arrangement of the substrate support of the present claims with the benefits achieved by such an arrangement as described in the present specification.

The protrusion shown in FIG. 2 of the reference is an abnormal growth generated on the processed substrate face and is not related to the substrate support member in any way.

In other words, ULVAC Japan Ltd. discloses the following:

- (1) Regulating the pressure to lower than atmospheric pressure during loading of the substrate support member supporting the substrate from the prechamber into the processing chamber.
- (2) Depositing a thin film on the substrate by CVD method.

However, ULVAC Japan Ltd. does not teach or suggest the following:

"The substrate support member contains a support section, formed as protrusion on the substrate support member and arranged to contact the substrate, and a receiving section installed below said support section and extending outwards from a section of the outer periphery of the support section."

The independent claims have been amended to clarify the invention and specify the above distinctions.

In view of the aforementioned amendments and accompanying remarks, Claims 1-18, as amended, are believed to be patentable and in condition for allowance, which action, at an early date, is requested.

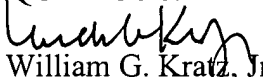
If, for any reason, it is felt that this application is not now in condition for allowance, the Examiner is requested to contact the applicants undersigned attorney at the telephone number indicated below to arrange for an interview to expedite the disposition of this case.

U.S. Patent Application Serial No. **10/517,765**  
Response to OA dated February 5, 2008

In the event that this paper is not timely filed, the applicants respectfully petition for an appropriate extension of time. Please charge any fees for such an extension of time and any other fees which may be due with respect to this paper, to Deposit Account No. 01-2340.

Respectfully submitted,

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Enclosure: Petition for Extension of Time